



80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET **POWERDI**

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
80V	$17m\Omega @ V_{GS} = 10V$	72A
	$21m\Omega$ @ $V_{GS} = 4.5V$	62A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Synchronous Rectifier
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features

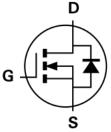
- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

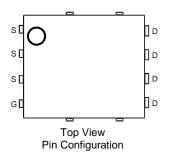
- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Bottom View Top View



Internal Schematic



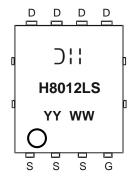
Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH8012LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



\\ \\ \\ = Manufacturer's Marking H8012LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 15 = 2015)WW = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_A = +25$ °C $T_A = +70$ °C	I _D	10 8.4	Α
Continuous Drain Current, V _{GS} = 10V (Note 7)	$T_C = +25$ °C $T_C = +70$ °C	I _D	72 60	Α
Maximum Continuous Body Diode Forward Current (Note 7)		Is	90	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	80	Α
Avalanche Current, L=0.1mH		I _{AS}	11.6	A
Avalanche Energy, L=0.1mH		E _{AS}	10.2	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	P_{D}	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta JA}$	57	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P_{D}	136	W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	1.1	°C/W
Operating and Storage Temperature Range		T_{J} , T_{STG}	-55 to +175	°C

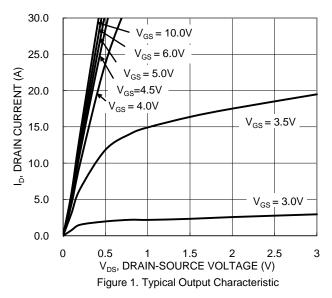
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	-	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		-	12.3	17		$V_{GS} = 10V, I_D = 12A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	15.1	21	mΩ	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V _{SD}	-	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C _{iss}	-	2051	-	pF	$V_{DS} = 40V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	-	189.9	-			
Reverse Transfer Capacitance	C _{rss}	-	24.6	-			
Gate Resistance	Rg	=	0.44	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	=	24.1	-		V _{DS} = 40V, I _D = 12A	
Total Gate Charge (V _{GS} = 10V)	Qg	-	46.8	-	nC		
Gate-Source Charge	Q _{gs}	-	6.9	-	iiC		
Gate-Drain Charge	Q_{gd}	-	12.2	-			
Turn-On Delay Time	t _{D(ON)}	-	5.8	-		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 12A, R_{G} = 1.6\Omega$	
Turn-On Rise Time	t _R	-	6.5	-			
Turn-Off Delay Time	t _{D(OFF)}	=	17.3	-	ns		
Turn-Off Fall Time	t _F	=	4.7	-			
Body Diode Reverse Recovery Time	t _{RR}	-	33.5	-	ns	1 12A di/dt 100A/v-	
Body Diode Reverse Recovery Charge	Q_{RR}	-	38.9	-	nC	$I_F = 12A$, di/dt = 100A/ μ s	

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.





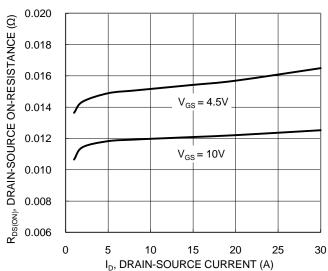


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

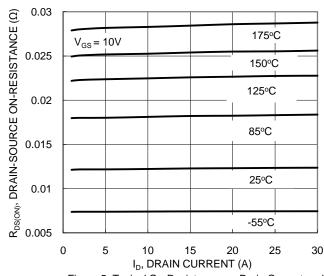
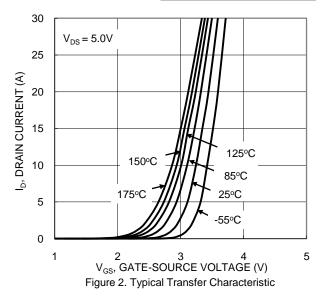
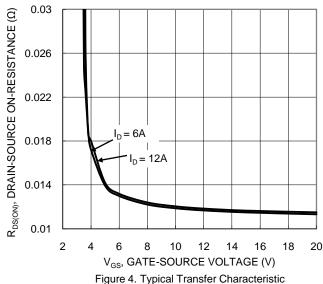


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



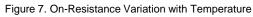


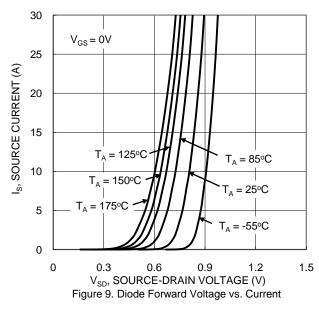
2.5 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2.3 2.1 1.9 $V_{GS} = 10V, I_{D} = 12A$ 1.7 1.5 1.3 1.1 $V_{GS} = 4.5V, I_{D} = 6A$ 0.9 0.7 0.5 75 100 125 50 T_.I, JUNCTION TEMPERATURE (°C)

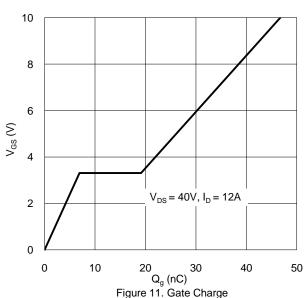
Figure 6. On-Resistance Variation with Temperature



$R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.035 0.03 0.025 $V_{GS} = 4.5V, I_D = 6A$ 0.02 0.015 0.01 $V_{GS} = 10V, I_{D} = 12A$ 0.005 0 -50 -25 25 50 75 100 125 150 175 T_J, JUNCTION TEMPERATURE (°C)







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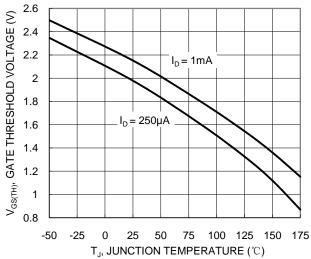
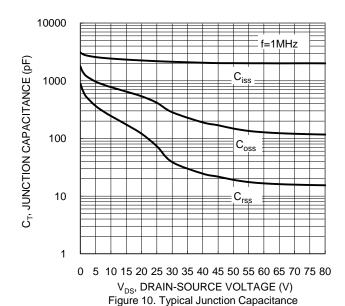


Figure 8. Gate Threshold Variation vs. Temperature



100 $R_{DS(ON)}$ Limited ID, DRAIN CURRENT (A) 10 $T_{J(MAX)} = 175^{\circ}C$ P_W=100µs T_C = 25°C Single Pulse DUT on 1*MRP Board $V_{GS} = 10V$ 0.1 $\begin{array}{ccc} & & & 1 & & 10 \\ V_{DS}, \, DRAIN-SOURCE \, VOLTAGE \, (V) \end{array}$ 0.1 100 Figure 12. SOA, Safe Operation Area



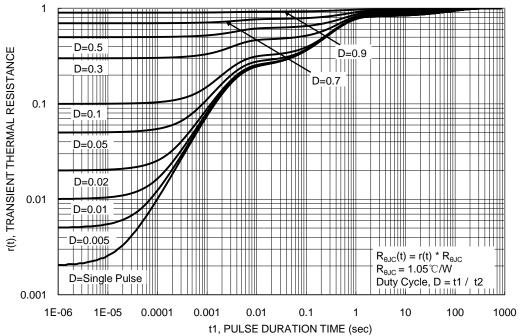


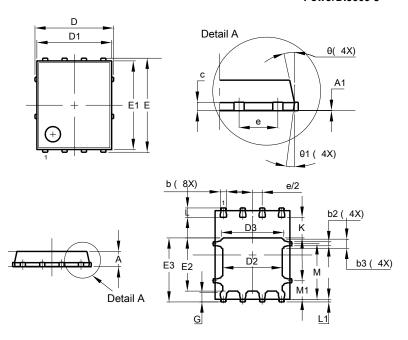
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

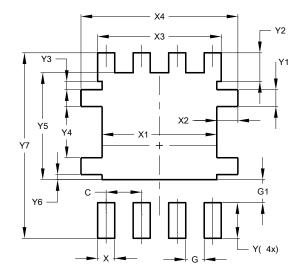


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05		
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D	,	5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC	,	
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е	1.27 BSC			
G	0.51	0.71	0.61	
K	0.51			
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12º	11º	
Θ1	6º	8º	7º	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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